



# **isc Silicon NPN Power Transistor**

#### **DESCRIPTION**

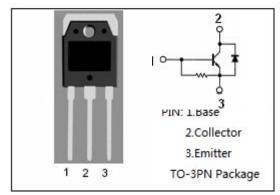
- · High Breakdown Voltage-
  - : V<sub>CBO</sub>= 1500V (Min)
- · High Switching Speed
- Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

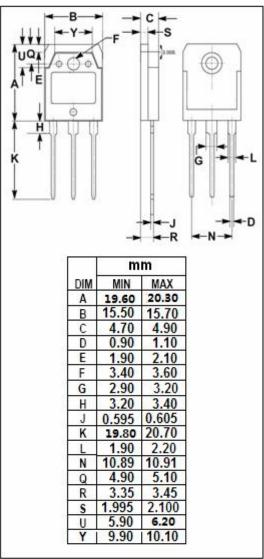
### **APPLICATIONS**

· Designed for horizontal output applications.

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	1500	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7	V	
I <sub>C</sub>	Collector Current- Continuous	2.5	Α	
Іср	Collector Current-Pulse	10	Α	
Pc	Collector Power Dissipation @ T <sub>C</sub> = 25 °C	50	W	
TJ	Junction Temperature	150	$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}\!\mathbb{C}$	







### isc Silicon NPN Power Transistor

2SD1396

#### **ELECTRICAL CHARACTERISTICS**

T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	1500			V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; R <sub>BE</sub> = ∞	800			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 200mA; I <sub>C</sub> = 0	7			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.6A			8.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.6A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			10	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0	40		130	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V	8			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V		3		MHz
V <sub>ECF</sub>	C-E Diode Forward Voltage	I <sub>F</sub> = 2.5A			2.0	V
tf	Fall Time	I <sub>C</sub> = 2A, I <sub>B1</sub> = 0.6A, I <sub>B2</sub> = 1.2A; R <sub>L</sub> = 100 Ω; V <sub>CC</sub> = 200V			0.7	μS

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